

# 74LVC2G14-Q100

Dual inverting Schmitt trigger with 5 V tolerant input

Rev. 1 — 15 November 2013

Product data sheet

## 1. General description

The 74LVC2G14-Q100 provides two inverting buffers with Schmitt-trigger input. It can transform slowly changing input signals into sharply defined, jitter-free output signals.

The inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device in a mixed 3.3 V and 5 V environment. Schmitt-trigger action at the inputs makes the circuit tolerant of slower input rise and fall time. This device is fully specified for partial power-down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

## 2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - ◆ Specified from  $-40\text{ }^{\circ}\text{C}$  to  $+85\text{ }^{\circ}\text{C}$  and from  $-40\text{ }^{\circ}\text{C}$  to  $+125\text{ }^{\circ}\text{C}$
- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant inputs for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
  - ◆ JESD8-7 (1.65 V to 1.95 V)
  - ◆ JESD8-5 (2.3 V to 2.7 V)
  - ◆ JESD8B/JESD36 (2.7 V to 3.6 V)
- ESD protection:
  - ◆ MIL-STD-883, method 3015 exceeds 2000 V
  - ◆ HBM JESD22-A114F exceeds 2000 V
  - ◆ MM JESD22-A115-A exceeds 200 V ( $C = 200\text{ pF}$ ,  $R = 0\text{ }\Omega$ )
- $\pm 24\text{ mA}$  output drive ( $V_{CC} = 3.0\text{ V}$ )
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Unlimited rise and fall times
- Input accepts voltages up to 5 V
- Multiple package options

## 3. Applications

- Wave and pulse shaper



- Astable multivibrator
- Monostable multivibrator

4. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVC2G14GW-Q100	−40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363
74LVC2G14GV-Q100	−40 °C to +125 °C	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457

5. Marking

Table 2. Marking codes

Type number	Marking code <sup>[1]</sup>
74LVC2G14GW-Q100	VK
74LVC2G14GV-Q100	V14

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

6. Functional diagram

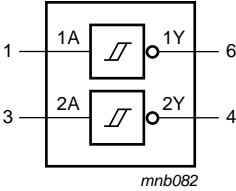


Fig 1. Logic symbol

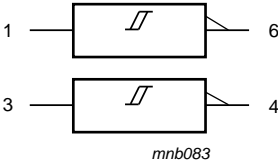


Fig 2. IEC logic symbol

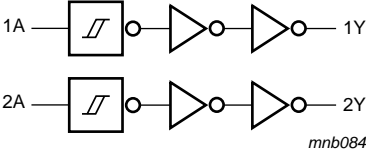


Fig 3. Logic diagram

7. Pinning information

7.1 Pinning

74LVC2G14-Q100

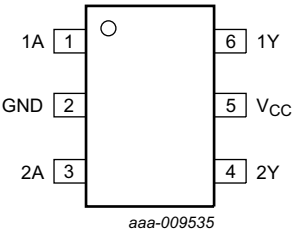


Fig 4. Pin configuration SOT363 and SOT457

## 7.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A	1	data input
GND	2	ground (0 V)
2A	3	data input
2Y	4	data output
V <sub>CC</sub>	5	supply voltage
1Y	6	data input

## 8. Functional description

Table 4. Function table<sup>[1]</sup>

Input	Output
nA	nY
L	H
H	L

[1] H = HIGH voltage level;  
L = LOW voltage level.

## 9. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+6.5	V
$I_{IK}$	input clamping current	$V_I < 0$ V	-50	-	mA
$V_I$	input voltage		[1] -0.5	+6.5	V
$I_{OK}$	output clamping current	$V_O > V_{CC}$ or $V_O < 0$ V	-	$\pm 50$	mA
$V_O$	output voltage	Active mode	[1][2] -0.5	$V_{CC} + 0.5$	V
		Power-down mode	[1][2] -0.5	+6.5	V
$I_O$	output current	$V_O = 0$ V to $V_{CC}$	-	$\pm 50$	mA
$I_{CC}$	supply current		-	100	mA
$I_{GND}$	ground current		-100	-	mA
$P_{tot}$	total power dissipation	$T_{amb} = -40$ °C to $+125$ °C	[3] -	250	mW
$T_{stg}$	storage temperature		-65	+150	°C

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When  $V_{CC} = 0$  V (Power-down mode), the output voltage can be 5.5 V in normal operation.

[3] For SC-88 and TSOP6 packages: above 87.5 °C the value of  $P_{tot}$  derates linearly with 4.0 mW/K.

## 10. Recommended operating conditions

**Table 6. Recommended operating conditions**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CC}$	supply voltage		1.65	-	5.5	V
$V_I$	input voltage		0	-	5.5	V
$V_O$	output voltage	Active mode	0	-	$V_{CC}$	V
		Power-down mode; $V_{CC} = 0$ V	0	-	5.5	V
$T_{amb}$	ambient temperature		-40	-	+125	°C

## 11. Static characteristics

**Table 7. Static characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ <sup>[1]</sup>	Max	Unit
<b>T<sub>amb</sub> = -40 °C to +85 °C</b>						
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = -100 µA; V <sub>CC</sub> = 1.65 V to 5.5 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -4 mA; V <sub>CC</sub> = 1.65 V	1.2	-	-	V
		I <sub>O</sub> = -8 mA; V <sub>CC</sub> = 2.3 V	1.9	-	-	V
		I <sub>O</sub> = -12 mA; V <sub>CC</sub> = 2.7 V	2.2	-	-	V
		I <sub>O</sub> = -24 mA; V <sub>CC</sub> = 3.0 V	2.3	-	-	V
		I <sub>O</sub> = -32 mA; V <sub>CC</sub> = 4.5 V	3.8	-	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = 100 µA; V <sub>CC</sub> = 1.65 V to 5.5 V	-	-	0.1	V
		I <sub>O</sub> = 4 mA; V <sub>CC</sub> = 1.65 V	-	-	0.45	V
		I <sub>O</sub> = 8 mA; V <sub>CC</sub> = 2.3 V	-	-	0.3	V
		I <sub>O</sub> = 12 mA; V <sub>CC</sub> = 2.7 V	-	-	0.4	V
		I <sub>O</sub> = 24 mA; V <sub>CC</sub> = 3.0 V	-	-	0.55	V
		I <sub>O</sub> = 32 mA; V <sub>CC</sub> = 4.5 V	-	-	0.55	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 0 V to 5.5 V	-	±0.1	±5	µA
I <sub>OFF</sub>	power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 5.5 V; V <sub>CC</sub> = 0 V	-	±0.1	±10	µA
I <sub>CC</sub>	supply current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 1.65 V to 5.5 V; I <sub>O</sub> = 0 A	-	0.1	10	µA
ΔI <sub>CC</sub>	additional supply current	V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 2.3 V to 5.5 V	-	5	500	µA
C <sub>I</sub>	input capacitance	V <sub>CC</sub> = 3.3 V; V <sub>I</sub> = GND to V <sub>CC</sub>	-	3.5	-	pF
<b>T<sub>amb</sub> = -40 °C to +125 °C</b>						
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = -100 µA; V <sub>CC</sub> = 1.65 V to 5.5 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -4 mA; V <sub>CC</sub> = 1.65 V	0.95	-	-	V
		I <sub>O</sub> = -8 mA; V <sub>CC</sub> = 2.3 V	1.7	-	-	V
		I <sub>O</sub> = -12 mA; V <sub>CC</sub> = 2.7 V	1.9	-	-	V
		I <sub>O</sub> = -24 mA; V <sub>CC</sub> = 3.0 V	2.0	-	-	V
		I <sub>O</sub> = -32 mA; V <sub>CC</sub> = 4.5 V	3.4	-	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = 100 µA; V <sub>CC</sub> = 1.65 V to 5.5 V	-	-	0.1	V
		I <sub>O</sub> = 4 mA; V <sub>CC</sub> = 1.65 V	-	-	0.7	V
		I <sub>O</sub> = 8 mA; V <sub>CC</sub> = 2.3 V	-	-	0.45	V
		I <sub>O</sub> = 12 mA; V <sub>CC</sub> = 2.7 V	-	-	0.6	V
		I <sub>O</sub> = 24 mA; V <sub>CC</sub> = 3.0 V	-	-	0.8	V
		I <sub>O</sub> = 32 mA; V <sub>CC</sub> = 4.5 V	-	-	0.8	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 0 V to 5.5 V	-	-	±20	µA

**Table 7.** Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ [1]	Max	Unit
$I_{OFF}$	power-off leakage current	$V_I$ or $V_O = 5.5$ V; $V_{CC} = 0$ V	-	-	$\pm 20$	$\mu$ A
$I_{CC}$	supply current	$V_I = 5.5$ V or GND; $V_{CC} = 1.65$ V to 5.5 V; $I_O = 0$ A	-	-	40	$\mu$ A
$\Delta I_{CC}$	additional supply current	$V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 2.3$ V to 5.5 V	-	-	5000	$\mu$ A

[1] All typical values are measured at maximum  $V_{CC}$  and  $T_{amb} = 25$  °C.**Table 8.** Transfer characteristicsVoltages are referenced to GND (ground = 0 V; for test circuit, see [Figure 6](#))

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ [1]	Max	Min	Max	
$V_{T+}$	positive-going threshold voltage	see <a href="#">Figure 7</a> and <a href="#">Figure 8</a>						
		$V_{CC} = 1.8$ V	0.70	1.10	1.50	0.70	1.70	V
		$V_{CC} = 2.3$ V	1.00	1.40	1.80	1.00	2.00	V
		$V_{CC} = 3.0$ V	1.30	1.76	2.20	1.30	2.40	V
		$V_{CC} = 4.5$ V	1.90	2.47	3.10	1.90	3.30	V
		$V_{CC} = 5.5$ V	2.20	2.91	3.60	2.20	3.80	V
$V_{T-}$	negative-going threshold voltage	see <a href="#">Figure 7</a> and <a href="#">Figure 8</a>						
		$V_{CC} = 1.8$ V	0.25	0.61	0.90	0.25	1.10	V
		$V_{CC} = 2.3$ V	0.40	0.80	1.15	0.40	1.35	V
		$V_{CC} = 3.0$ V	0.60	1.04	1.50	0.60	1.70	V
		$V_{CC} = 4.5$ V	1.00	1.55	2.00	1.00	2.20	V
		$V_{CC} = 5.5$ V	1.20	1.86	2.30	1.20	2.50	V
$V_H$	hysteresis voltage	$(V_{T+} - V_{T-})$ ; see <a href="#">Figure 7</a> , <a href="#">Figure 8</a> and <a href="#">Figure 9</a>						
		$V_{CC} = 1.8$ V	0.15	0.49	1.00	0.15	1.20	V
		$V_{CC} = 2.3$ V	0.25	0.60	1.10	0.25	1.30	V
		$V_{CC} = 3.0$ V	0.40	0.73	1.20	0.40	1.40	V
		$V_{CC} = 4.5$ V	0.60	0.92	1.50	0.60	1.70	V
		$V_{CC} = 5.5$ V	0.70	1.02	1.70	0.70	1.90	V

[1] All typical values are measured at  $T_{amb} = 25$  °C

## 12. Dynamic characteristics

**Table 9. Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V); for test circuit, see [Figure 6](#).

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	
$t_{pd}$	propagation delay	nA to nY; see <a href="#">Figure 5</a> <sup>[2]</sup>						
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	1.0	5.6	11.0	1.0	12.0	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	0.5	3.7	6.5	0.5	7.2	ns
		$V_{CC} = 2.7 \text{ V}$	0.5	4.1	7.0	0.5	7.7	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	0.5	3.9	6.0	0.5	6.7	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0.5	2.7	4.3	0.5	4.7	ns
$C_{PD}$	power dissipation capacitance	$V_I = \text{GND to } V_{CC}; V_{CC} = 3.3 \text{ V}$ <sup>[3]</sup>	-	18.1	-	-	-	pF

[1] Typical values are measured at  $T_{amb} = 25 \text{ °C}$  and  $V_{CC} = 1.8 \text{ V}, 2.5 \text{ V}, 2.7 \text{ V}, 3.3 \text{ V}$  and  $5.0 \text{ V}$  respectively.

[2]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

[3]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu\text{W}$ ).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$  where:

$f_i$  = input frequency in MHz;

$f_o$  = output frequency in MHz;

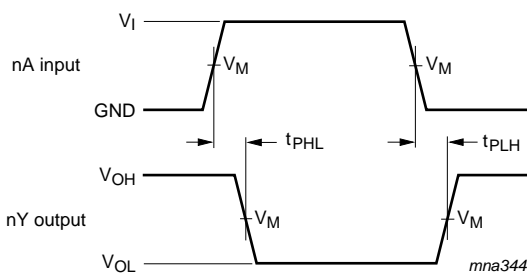
$C_L$  = output load capacitance in pF;

$V_{CC}$  = supply voltage in V;

$N$  = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of outputs.

## 13. Waveforms



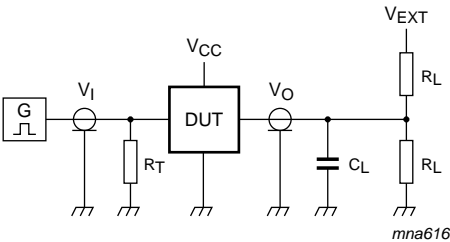
Measurement points are given in [Table 10](#).

$V_{OL}$  and  $V_{OH}$  are typical output voltage levels that occur with the output load.

**Fig 5. The data input (nA) to output (nY) propagation delays**

Table 10. Measurement points

Supply voltage	Input	Output
V <sub>CC</sub>	V <sub>M</sub>	V <sub>M</sub>
1.65 V to 1.95 V	0.5 × V <sub>CC</sub>	0.5 × V <sub>CC</sub>
2.3 V to 2.7 V	0.5 × V <sub>CC</sub>	0.5 × V <sub>CC</sub>
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	0.5 × V <sub>CC</sub>	0.5 × V <sub>CC</sub>



Test data is given in [Table 11](#).  
Definitions for test circuit:  
R<sub>L</sub> = Load resistance.  
C<sub>L</sub> = Load capacitance including jig and probe capacitance.  
R<sub>T</sub> = Termination resistance should be equal to the output impedance Z<sub>o</sub> of the pulse generator.  
V<sub>EXT</sub> = External voltage for measuring switching times.

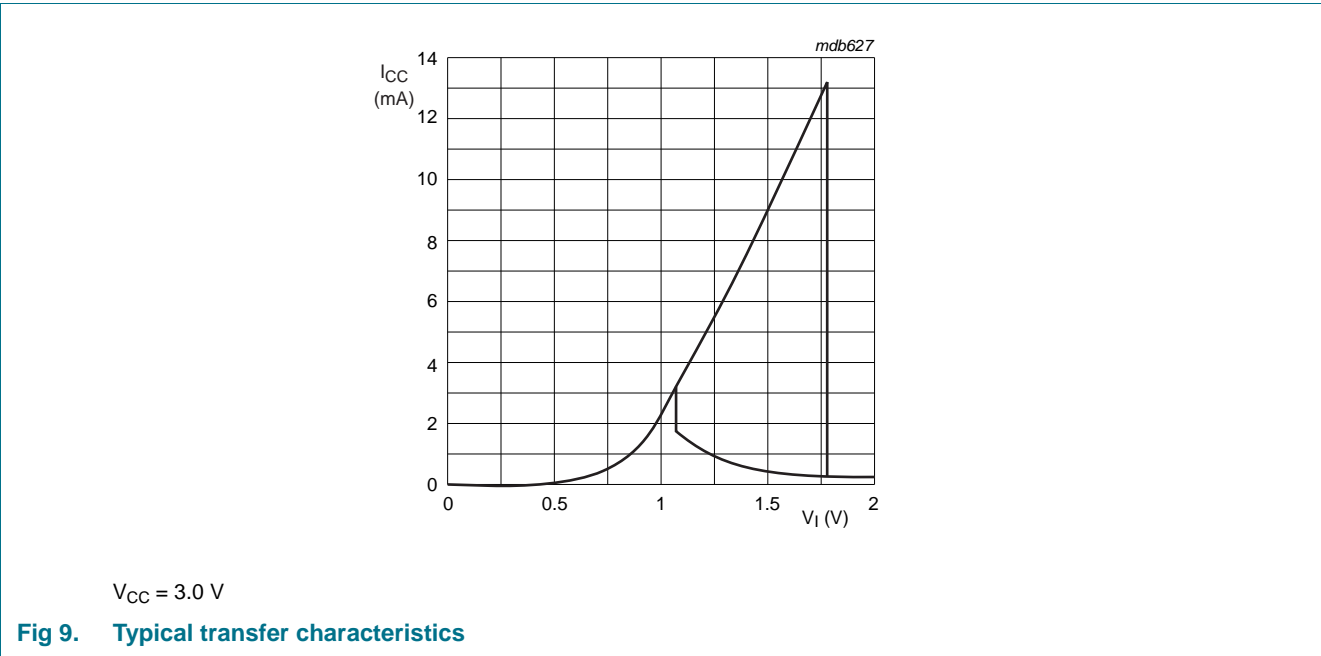
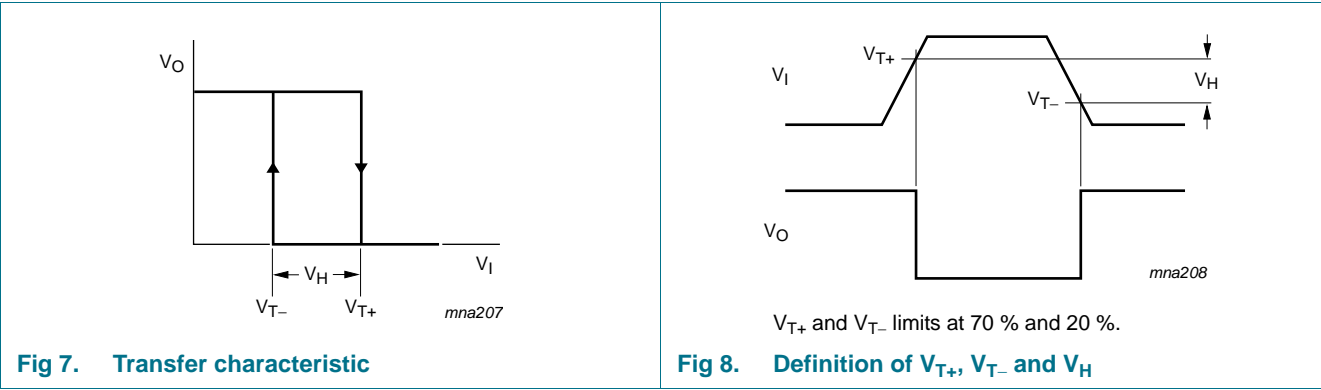
Fig 6. Load circuitry for switching times

Table 11. Test data

Supply voltage	Input		Load		V <sub>EXT</sub>
V <sub>CC</sub>	V <sub>I</sub>	t <sub>r</sub> = t <sub>f</sub>	C <sub>L</sub>	R <sub>L</sub>	t <sub>PLH</sub> , t <sub>PHL</sub>
1.65 V to 1.95 V	V <sub>CC</sub>	≤ 2.0 ns	30 pF	1 kΩ	open
2.3 V to 2.7 V	V <sub>CC</sub>	≤ 2.0 ns	30 pF	500 Ω	open
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open
4.5 V to 5.5 V	V <sub>CC</sub>	≤ 2.5 ns	50 pF	500 Ω	open



14. Waveforms transfer characteristics



## 15. Application information

The slow input rise and fall times cause additional power dissipation, which can be calculated using the following formula:

$$P_{\text{add}} = f_i \times (t_r \times \Delta I_{\text{CC(AV)}} + t_f \times \Delta I_{\text{CC(AV)}}) \times V_{\text{CC}} \text{ where:}$$

$P_{\text{add}}$  = additional power dissipation ( $\mu\text{W}$ );

$f_i$  = input frequency (MHz);

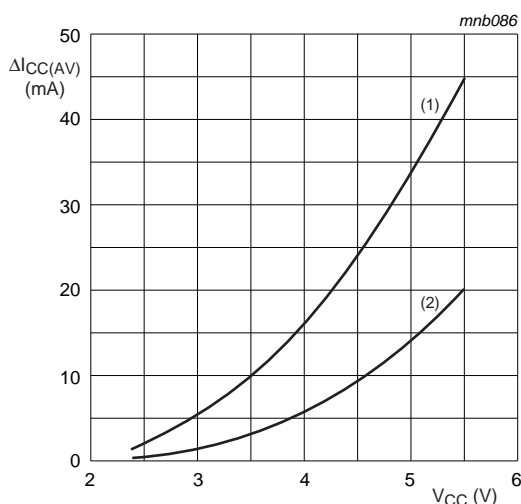
$t_r$  = input rise time (ns); 10 % to 90 %;

$t_f$  = input fall time (ns); 90 % to 10 %;

$\Delta I_{\text{CC(AV)}}$  = average additional supply current ( $\mu\text{A}$ ).

$\Delta I_{\text{CC(AV)}}$  differs with positive or negative input transitions, as shown in [Figure 10](#).

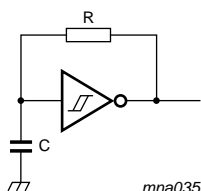
An example of a relaxation circuit using the 74LVC2G14-Q100 is shown in [Figure 11](#).



Linear change of  $V_I$  between 0.8 V to 2.0 V. All values given are typical unless otherwise specified.

- (1) Positive-going edge.
- (2) Negative-going edge.

**Fig 10. Average  $I_{\text{CC}}$  as a function of  $V_{\text{CC}}$**



$$f = \frac{1}{T} \approx \frac{1}{0.8 \times RC}$$

**Fig 11. Relaxation oscillator**

16. Package outline

Plastic surface-mounted package; 6 leads

SOT363

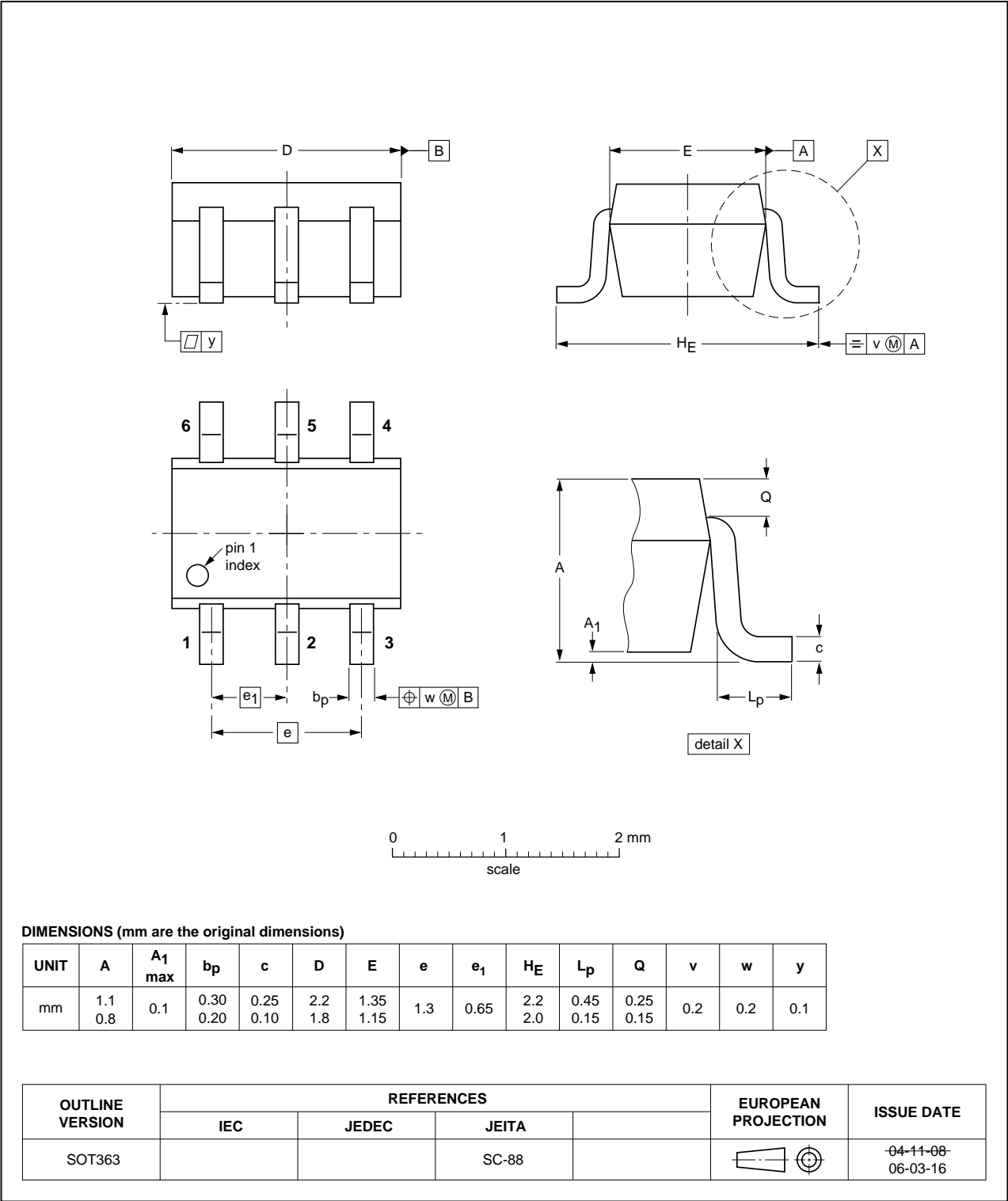


Fig 12. Package outline SOT363 (SC-88)

Plastic surface-mounted package (TSOP6); 6 leads

SOT457

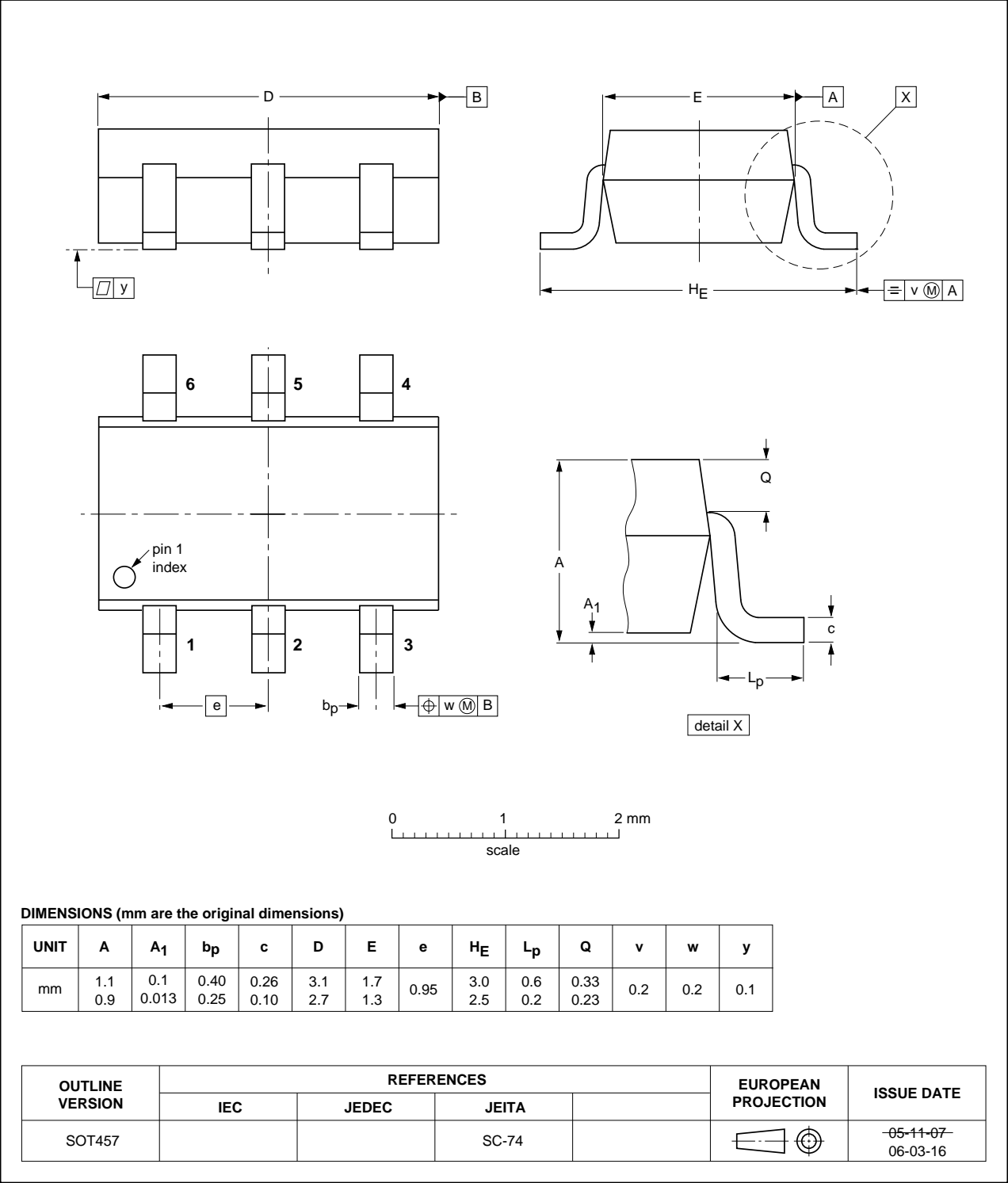


Fig 13. Package outline SOT457 (TSOP6)

## 17. Abbreviations

Table 12. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
TTL	Transistor-Transistor Logic
HBM	Human Body Model
ESD	ElectroStatic Discharge
MIL	Military
MM	Machine Model
DUT	Device Under Test

## 18. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC2G14_Q100 v.1	20131115	Product data sheet	-	-

## 19. Legal information

### 19.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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